



BF556A; BF556B; BF556C

N-channel silicon junction field-effect transistors

Rev. 4 — 15 September 2011

Product data sheet

1. Product profile

1.1 General description

N-channel symmetrical silicon junction field-effect transistors in a SOT23 package.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features and benefits

- Low leakage level (typ. 500 fA)
- High gain
- Low cut-off voltage.

1.3 Applications

- Impedance converters in e.g. electret microphones and infrared detectors
- VHF amplifiers in oscillators and mixers.

1.4 Quick reference data

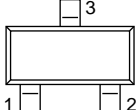

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage (DC)		-	-	±30	V
V_{GSoff}	gate-source cut-off voltage	$I_D = 200 \mu A$; $V_{DS} = 15 V$	-0.5	-	-7.5	V
I_{DSS}	drain current	$V_{GS} = 0 V$; $V_{DS} = 15 V$				
		BF556A	3	-	7	mA
		BF556B	6	-	13	mA
		BF556C	11	-	18	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25 \text{ }^\circ C$	-	-	250	mW
$ y_{fs} $	forward transfer admittance	$V_{GS} = 0 V$; $V_{DS} = 15 V$	4.5	-	-	mS



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	source (s)		 <i>sym054</i>
2	drain (d)		
3	gate (g)		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BF556A	-	plastic surface mounted package; 3 leads	SOT23
BF556B			
BF556C			

4. Marking

Table 4. Marking

Type number	Marking code ^[1]
BF556A	24*
BF556B	25*
BF556C	26*

[1] * = p: made in Hong Kong.

* = t: made in Malaysia.

* = W: made in China.

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)		-	± 30	V
V_{GSO}	gate-source voltage	open drain	-	-30	V
V_{GDO}	gate-drain voltage (DC)	open source	-	-30	V
I_G	forward gate current (DC)		-	10	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[1]	250	mW
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-	150	°C

[1] Device mounted on an FR4 printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead 10 mm².

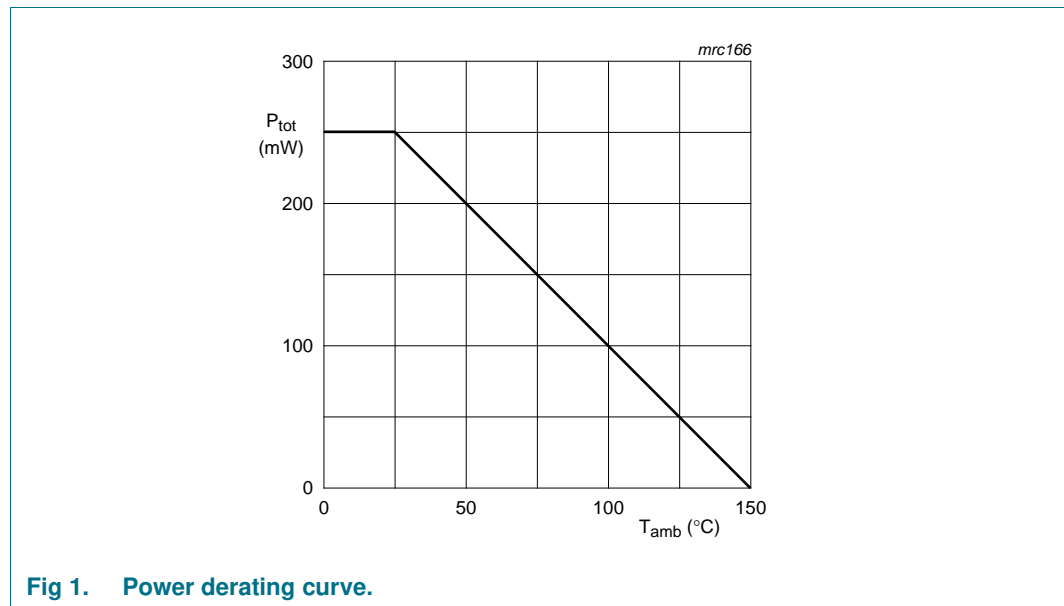


Fig 1. Power derating curve.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient		[1] 500	K/W

[1] Device mounted on an FR4 printed-circuit board, maximum lead length 4 mm; mounting pad for the drain lead 10 mm².

7. Static characteristics

Table 7. Static characteristics

$T_j = 25\text{ °C}$ unless otherwise specified.

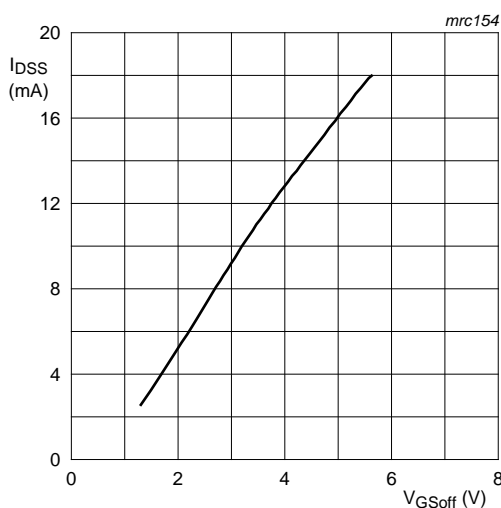
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)GSS}$	gate-source breakdown voltage	$I_G = -1\ \mu\text{A}$; $V_{DS} = 0\ \text{V}$	-30	-	-	V
V_{GSoff}	gate-source cut-off voltage	$I_D = 200\ \mu\text{A}$; $V_{DS} = 15\ \text{V}$	-0.5	-	-7.5	V
I_{DSS}	drain current	$V_{GS} = 0\ \text{V}$; $V_{DS} = 15\ \text{V}$				
		BF556A	3	-	7	mA
		BF556B	6	-	13	mA
	BF556C	11	-	18	mA	
I_{GSS}	gate-source leakage current	$V_{GS} = -20\ \text{V}$; $V_{DS} = 0\ \text{V}$	-	-0.5	-5000	pA
$ y_{fs} $	forward transfer admittance	$V_{GS} = 0\ \text{V}$; $V_{DS} = 15\ \text{V}$	4.5	-	-	mS
$ y_{os} $	common source output admittance	$V_{GS} = 0\ \text{V}$; $V_{DS} = 15\ \text{V}$	-	40	-	μS

8. Dynamic characteristics

Table 8. Dynamic characteristics

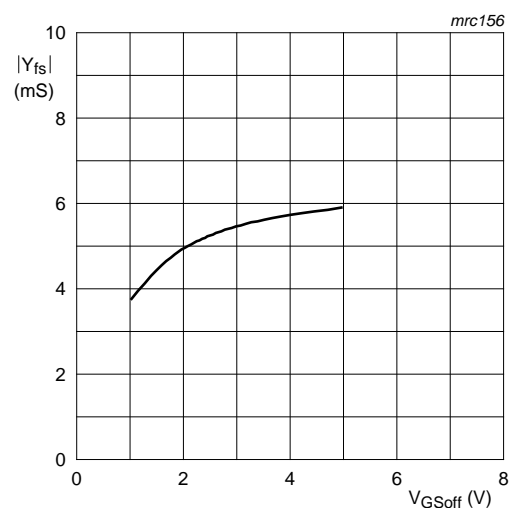
$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{iss}	input capacitance	$V_{DS} = 15\text{ V}; f = 1\text{ MHz}$				
		$V_{GS} = -10\text{ V}$	-	1.7	-	pF
		$V_{GS} = 0\text{ V}$	-	3	-	pF
C_{rss}	reverse transfer capacitance	$V_{DS} = 15\text{ V}; f = 1\text{ MHz}$				
		$V_{GS} = -10\text{ V}$	-	0.8	-	pF
		$V_{GS} = 0\text{ V}$	-	0.9	-	pF
g_{is}	common source input conductance	$V_{DS} = 10\text{ V}; I_D = 1\text{ mA}$				
		$f = 100\text{ MHz}$	-	15	-	μS
		$f = 450\text{ MHz}$	-	300	-	μS
g_{fs}	common source transfer conductance	$V_{DS} = 10\text{ V}; I_D = 1\text{ mA}$				
		$f = 100\text{ MHz}$	-	2	-	mS
		$f = 450\text{ MHz}$	-	1.8	-	mS
g_{rs}	common source reverse conductance	$V_{DS} = 10\text{ V}; I_D = 1\text{ mA}$				
		$f = 100\text{ MHz}$	-	-6	-	μS
		$f = 450\text{ MHz}$	-	-40	-	μS
g_{os}	common source output conductance	$V_{DS} = 10\text{ V}; I_D = 1\text{ mA}$				
		$f = 100\text{ MHz}$	-	30	-	μS
		$f = 450\text{ MHz}$	-	60	-	μS
V_n	equivalent input noise voltage	$V_{DS} = 10\text{ V}; I_D = 1\text{ mA};$ $f = 100\text{ Hz}$	-	40	-	$\text{nV}/\sqrt{\text{Hz}}$



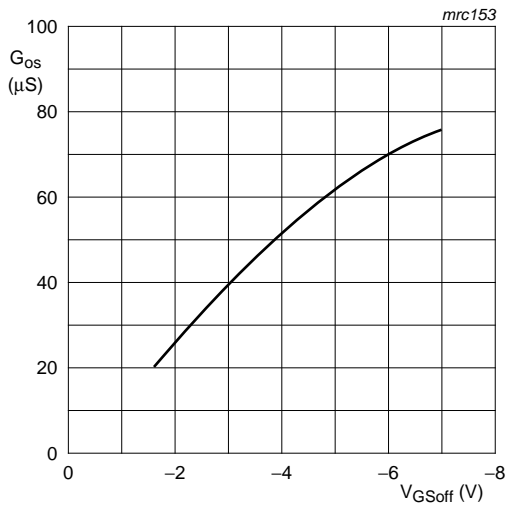
$V_{DS} = 15\text{ V}.$

Fig. 2. Drain current as a function of gate-source cut-off voltage; typical values.



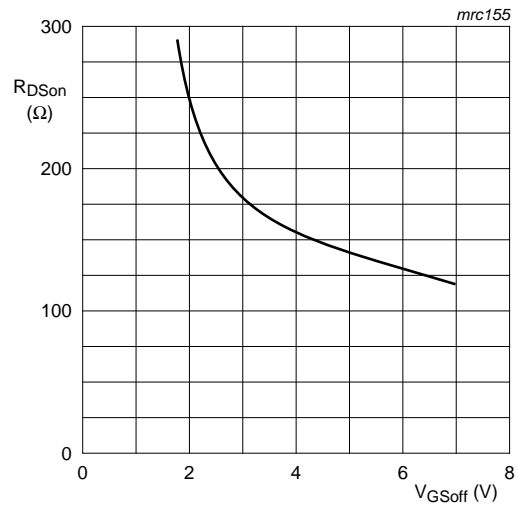
$V_{DS} = 15\text{ V}; I_D = 1\text{ }\mu\text{A}.$

Fig. 3. Forward transfer admittance as a function of gate-source cut-off voltage; typical values.



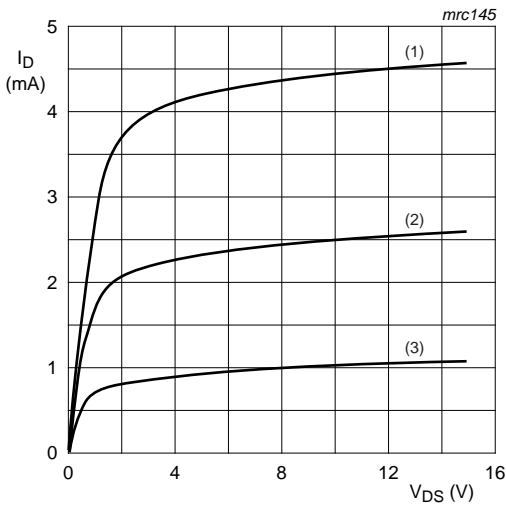
$V_{DS} = 15 \text{ V.}$

Fig 4. Common-source output conductance as a function of gate-source cut-off voltage; typical values.



$V_{DS} = 100 \text{ mV; } V_{GS} = 0 \text{ V.}$

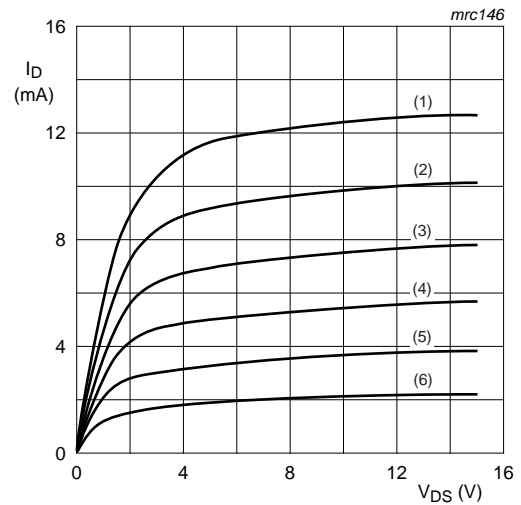
Fig 5. Drain-source on-state resistance as a function of gate-source cut-off voltage; typical values.



BF556A

- (1) $V_{GS} = 0 \text{ V.}$
- (2) $V_{GS} = -0.5 \text{ V.}$
- (3) $V_{GS} = -1.0 \text{ V.}$

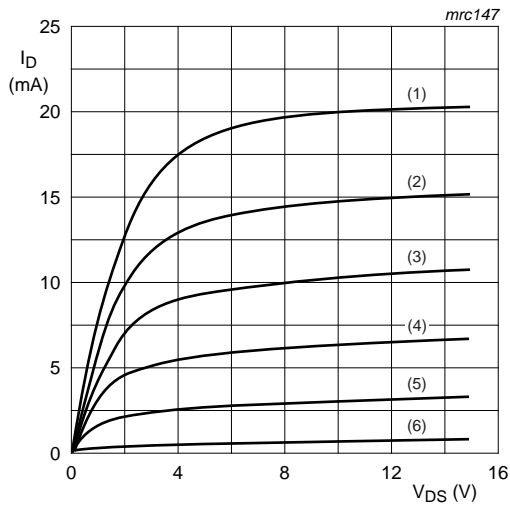
Fig 6. Typical output characteristics.



BF556B

- (1) $V_{GS} = 0 \text{ V.}$
- (2) $V_{GS} = -0.5 \text{ V.}$
- (3) $V_{GS} = -1.0 \text{ V.}$
- (4) $V_{GS} = -1.5 \text{ V.}$
- (5) $V_{GS} = -2.0 \text{ V.}$
- (6) $V_{GS} = -2.5 \text{ V.}$

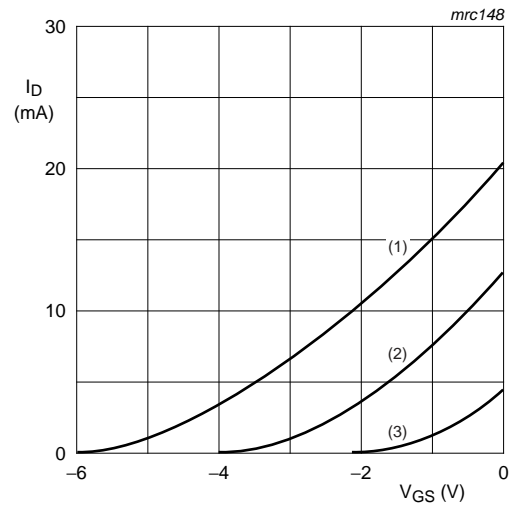
Fig 7. Typical output characteristics.



BF556C

- (1) $V_{GS} = 0\text{ V}$.
- (2) $V_{GS} = -1.0\text{ V}$.
- (3) $V_{GS} = -2.0\text{ V}$.
- (4) $V_{GS} = -3.0\text{ V}$.
- (5) $V_{GS} = -4.0\text{ V}$.
- (6) $V_{GS} = -5.0\text{ V}$.

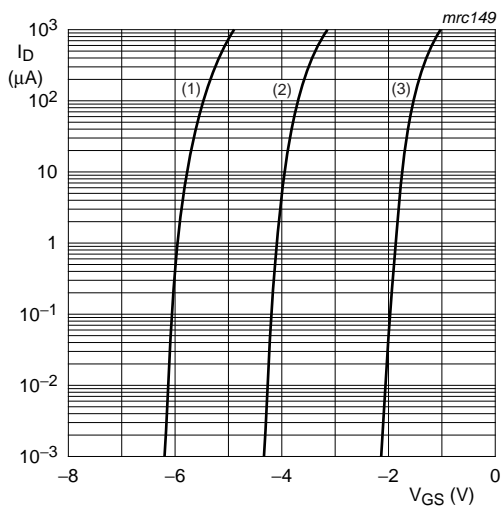
Fig 8. Typical output characteristics.



$V_{DS} = 15\text{ V}$.

- (1) BF556C.
- (2) BF556B.
- (3) BF556A.

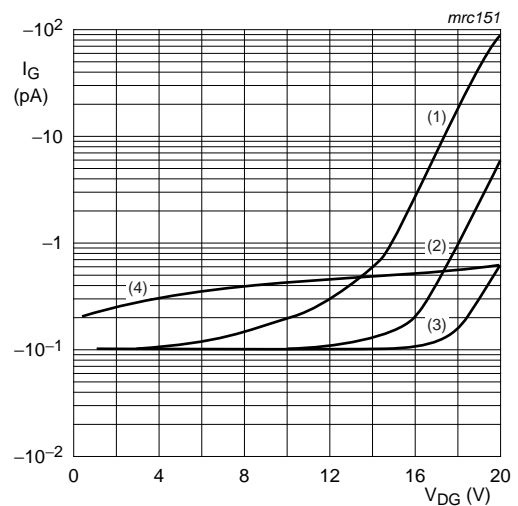
Fig 9. Typical input characteristics.



$V_{DS} = 15\text{ V}$.

- (1) BF556C.
- (2) BF556B.
- (3) BF556A.

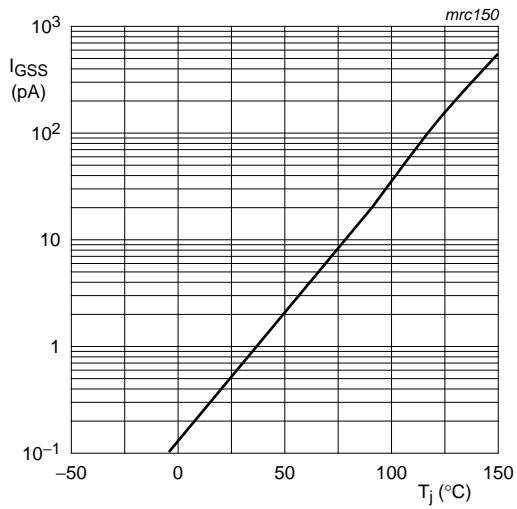
Fig 10. Drain current as a function of gate-source voltage; typical values.



$I_D = 10\text{ mA}$ only for BF556B and BF556C.

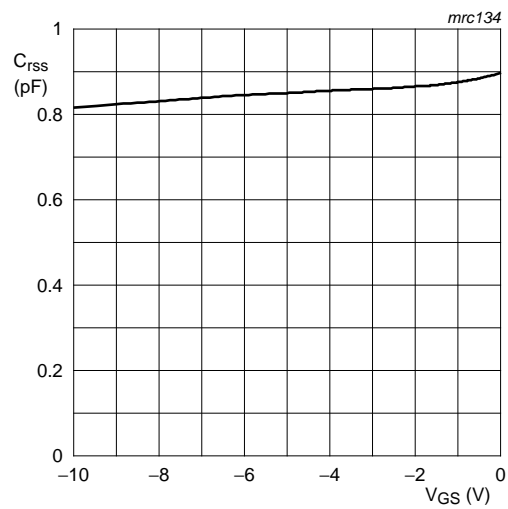
- (1) $I_D = 10\text{ mA}$.
- (2) $I_D = 1\text{ mA}$.
- (3) $I_D = 0.1\text{ mA}$.
- (4) I_{GSS} .

Fig 11. Gate current as a function of drain-gate voltage; typical values.



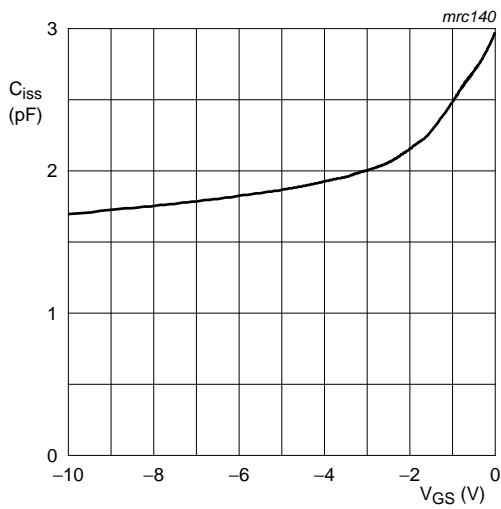
$V_{DS} = 0$ V; $V_{GS} = -20$ V.

Fig. 12. Gate current as a function of junction temperature; typical values.



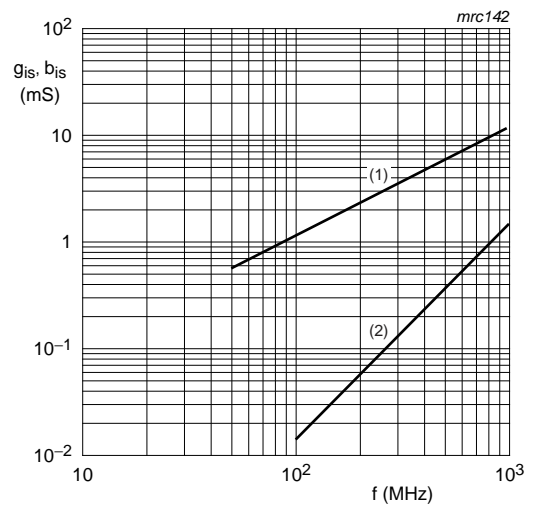
$V_{DS} = 15$ V.

Fig. 13. Reverse transfer capacitance; typical values.



$V_{DS} = 15$ V.

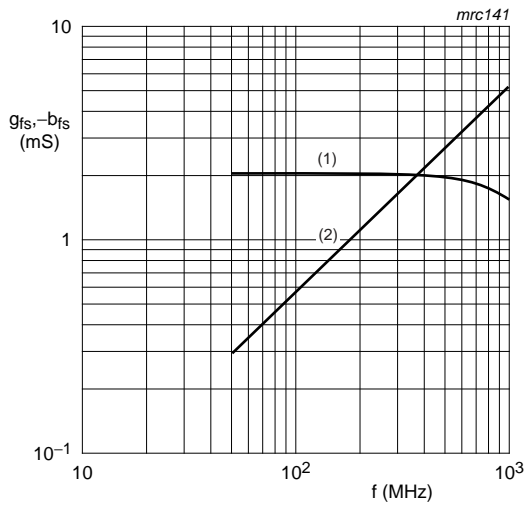
Fig. 14. Input capacitance; typical values.



$V_{DS} = 10$ V; $I_D = 1$ mA; $T_{amb} = 25$ °C.

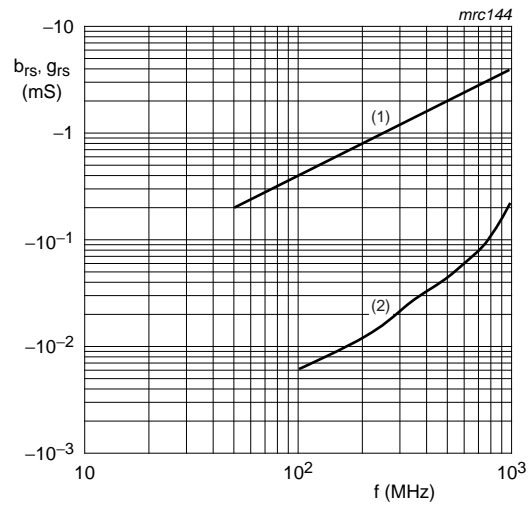
- (1) b_{is} .
- (2) g_{is} .

Fig. 15. Common-source input admittance; typical values.



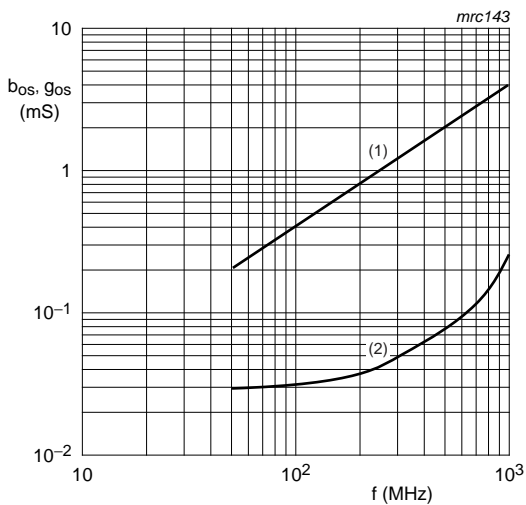
$V_{DS} = 10\text{ V}; I_D = 1\text{ mA}; T_{amb} = 25\text{ }^\circ\text{C}.$
 (1) g_{fs} .
 (2) $-b_{fs}$.

Fig 16. Common-source transfer admittance; typical values.



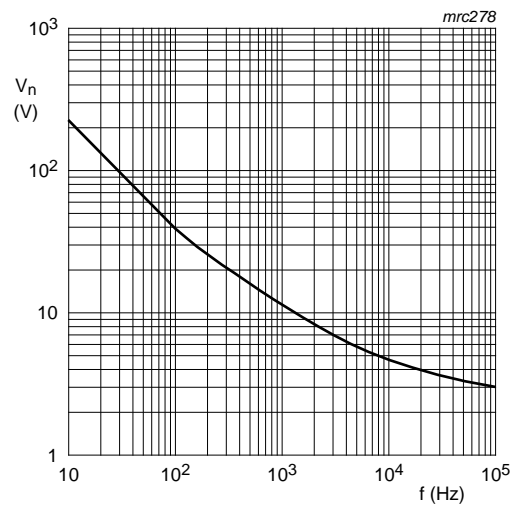
$V_{DS} = 10\text{ V}; I_D = 1\text{ mA}; T_{amb} = 25\text{ }^\circ\text{C}.$
 (1) b_{rs} .
 (2) g_{rs} .

Fig 17. Common-source reverse admittance; typical values.



$V_{DS} = 10\text{ V}; I_D = 1\text{ mA}; T_{amb} = 25\text{ }^\circ\text{C}.$
 (1) b_{os} .
 (2) g_{os} .

Fig 18. Common-source output admittance; typical values.



$V_{DS} = 10\text{ V}; I_D = 1\text{ mA}.$

Fig 19. Equivalent noise voltage as a function of frequency.

9. Package outline

Plastic surface-mounted package; 3 leads

SOT23

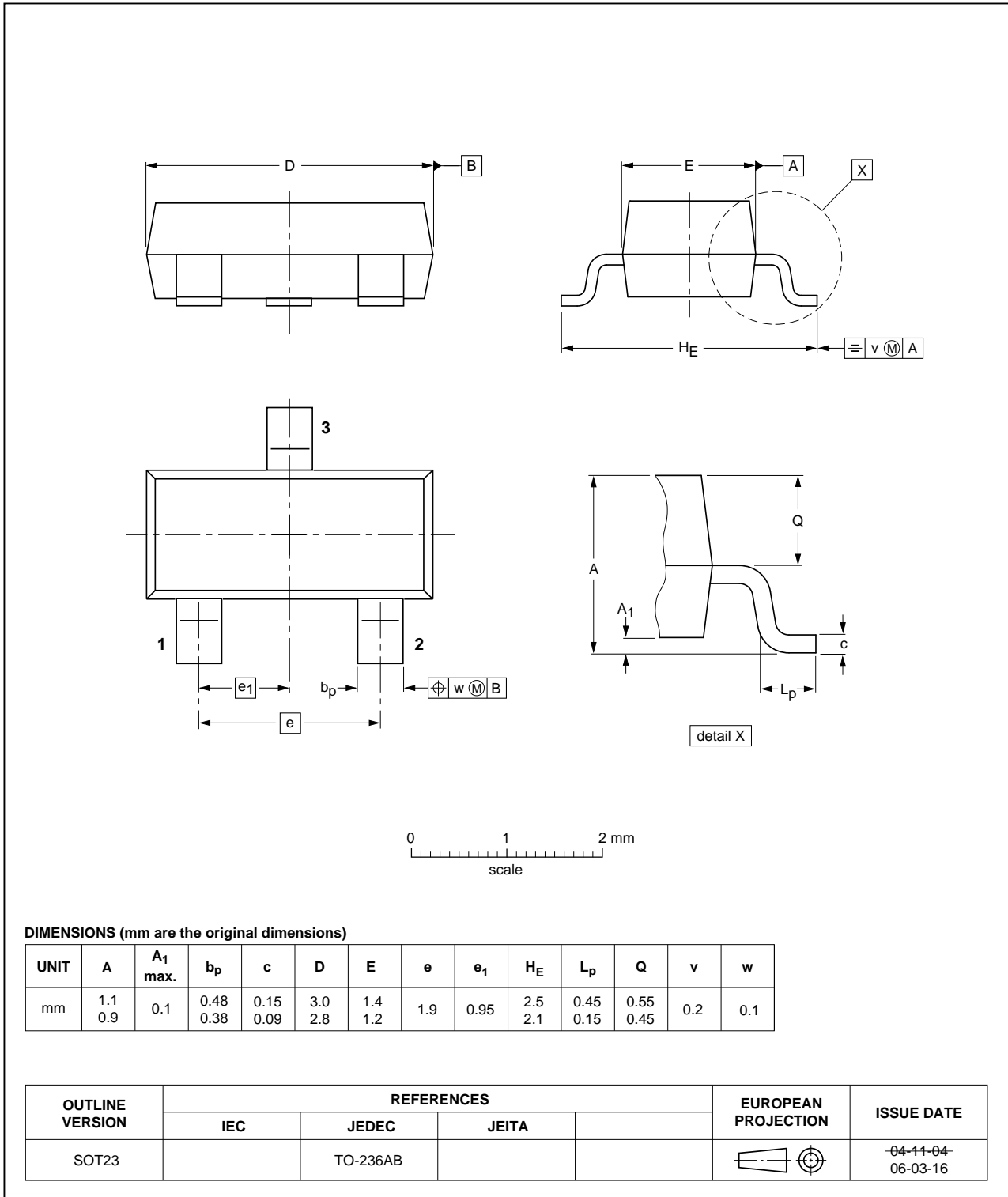


Fig 20. Package outline.

10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BF556A_BF556B_BF556C v.4	20110915	Product data sheet	-	BF556A_BF556B_BF556C v.3
Modifications:				
				<ul style="list-style-type: none">• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.• Legal texts have been adapted to the new company name where appropriate.• Package outline drawings have been updated to the latest version.
BF556A_BF556B_BF556C v.3 (9397 750 13393)	20040805	Product data sheet	-	BF556A-B-C v.2
BF556A-B-C v.2	19960729	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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